

# NTMFS4983NF

## Power MOSFET

30 V, 106 A, Single N-Channel, SO-8 FL

### Features

- Integrated Schottky Diode
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- CPU Power Delivery
- Synchronous Rectification for DC-DC Converters
- Low Side Switching
- Telecom Secondary Side Rectification

**MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise stated)

| Parameter                                                                                                                                                               |                      |                       | Symbol                            | Value       | Unit |
|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----------------------|-----------------------|-----------------------------------|-------------|------|
| Drain-to-Source Voltage                                                                                                                                                 |                      |                       | V <sub>DSS</sub>                  | 30          | V    |
| Gate-to-Source Voltage                                                                                                                                                  |                      |                       | V <sub>GS</sub>                   | ±20         | V    |
| Continuous Drain Current R <sub>θJA</sub> (Note 1)                                                                                                                      | Steady State         | T <sub>A</sub> = 25°C | I <sub>D</sub>                    | 30          | A    |
|                                                                                                                                                                         |                      | T <sub>A</sub> = 85°C |                                   | 22          |      |
| Power Dissipation R <sub>θJA</sub> (Note 1)                                                                                                                             |                      | T <sub>A</sub> = 25°C | P <sub>D</sub>                    | 3.13        | W    |
| Continuous Drain Current R <sub>θJA</sub> ≤ 10 sec                                                                                                                      |                      | T <sub>A</sub> = 25°C | I <sub>D</sub>                    | 48          | A    |
|                                                                                                                                                                         |                      | T <sub>A</sub> = 85°C |                                   | 34          |      |
| Power Dissipation R <sub>θJA</sub> , t ≤ 10 sec                                                                                                                         |                      | T <sub>A</sub> = 25°C | P <sub>D</sub>                    | 7.7         | W    |
| Continuous Drain Current R <sub>θJA</sub> (Note 2)                                                                                                                      |                      | T <sub>A</sub> = 25°C | I <sub>D</sub>                    | 22          | A    |
|                                                                                                                                                                         |                      | T <sub>A</sub> = 85°C |                                   | 16          |      |
| Power Dissipation R <sub>θJA</sub> (Note 2)                                                                                                                             |                      | T <sub>A</sub> = 25°C | P <sub>D</sub>                    | 1.7         | W    |
| Continuous Drain Current R <sub>θJC</sub> (Note 1)                                                                                                                      |                      | T <sub>C</sub> = 25°C | I <sub>D</sub>                    | 106         | A    |
|                                                                                                                                                                         |                      | T <sub>C</sub> = 85°C |                                   | 76          |      |
| Power Dissipation R <sub>θJC</sub> (Note 1)                                                                                                                             |                      | T <sub>C</sub> = 25°C | P <sub>D</sub>                    | 38          | W    |
| Pulsed Drain Current                                                                                                                                                    | t <sub>p</sub> =10μs | T <sub>A</sub> = 25°C | I <sub>DM</sub>                   | 320         | A    |
| Current limited by package                                                                                                                                              |                      | T <sub>A</sub> = 25°C | I <sub>Dmaxpkg</sub>              | 100         | A    |
| Operating Junction and Storage Temperature                                                                                                                              |                      |                       | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |
| Source Current (Body Diode)                                                                                                                                             |                      |                       | I <sub>S</sub>                    | 54          | A    |
| Drain to Source dV/dt                                                                                                                                                   |                      |                       | dV/dt                             | 6           | V/ns |
| Single Pulse Drain-to-Source Avalanche Energy (V <sub>DD</sub> = 50 V, V <sub>GS</sub> = 10 V, I <sub>L</sub> = 45 A <sub>pk</sub> , L = 0.1 mH, R <sub>G</sub> = 25 Ω) |                      |                       | EAS                               | 101         | mJ   |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)                                                                                                       |                      |                       | T <sub>L</sub>                    | 260         | °C   |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

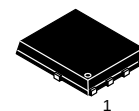
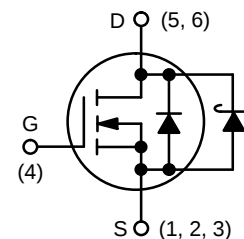


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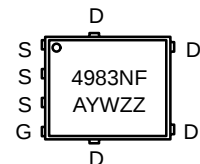
| $V_{(BR)DSS}$ | $R_{DS(ON)} \text{ MAX}$ | $I_D \text{ MAX}$ |
|---------------|--------------------------|-------------------|
| 30 V          | 2.1 m $\Omega$ @ 10 V    | 106 A             |
|               | 3.1 m $\Omega$ @ 4.5 V   |                   |

### N-CHANNEL MOSFET



**SO-8 FLAT LEAD  
CASE 488AA  
STYLE 1**

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

### ORDERING INFORMATION

| Device         | Package          | Shipping†          |
|----------------|------------------|--------------------|
| NTMFS4983NFT1G | SO-8FL (Pb-Free) | 1500 / Tape & Reel |
| NTMFS4983NFT3G | SO-8FL (Pb-Free) | 5000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter                                   | Symbol          | Value | Unit |
|---------------------------------------------|-----------------|-------|------|
| Junction-to-Case (Drain)                    | $R_{\theta JC}$ | 3.3   | °C/W |
| Junction-to-Ambient – Steady State (Note 1) | $R_{\theta JA}$ | 40    |      |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 74    |      |
| Junction-to-Ambient – $t \leq 10$ sec       | $R_{\theta JA}$ | 16.3  |      |

1. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm<sup>2</sup>.

ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

## OFF CHARACTERISTICS

|                                                           |                   |                                                                         |    |    |      |       |
|-----------------------------------------------------------|-------------------|-------------------------------------------------------------------------|----|----|------|-------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 1.0\text{ mA}$                              | 30 |    |      | V     |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | $I_D = 10\text{ mA}$ , referenced to $25^\circ\text{C}$                 |    | 15 |      | mV/°C |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}, V_{DS} = 24\text{ V}$<br>$T_J = 25^\circ\text{C}$ |    |    | 500  | μA    |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$                         |    |    | ±100 | nA    |

## ON CHARACTERISTICS (Note 3)

|                                            |                  |                                                         |     |     |     |       |
|--------------------------------------------|------------------|---------------------------------------------------------|-----|-----|-----|-------|
| Gate Threshold Voltage                     | $V_{GS(TH)}$     | $V_{GS} = V_{DS}, I_D = 1.0\text{ mA}$                  | 1.2 | 1.7 | 2.3 | V     |
| Negative Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | $I_D = 10\text{ mA}$ , referenced to $25^\circ\text{C}$ |     | 5.0 |     | mV/°C |
| Drain-to-Source On Resistance              | $R_{DS(on)}$     | $V_{GS} = 10\text{ V}$<br>$I_D = 30\text{ A}$           |     | 1.6 | 2.1 | mΩ    |
|                                            |                  | $I_D = 15\text{ A}$                                     |     | 1.6 |     |       |
|                                            |                  | $V_{GS} = 4.5\text{ V}$<br>$I_D = 30\text{ A}$          |     | 2.5 | 3.1 |       |
|                                            |                  | $I_D = 15\text{ A}$                                     |     | 2.5 |     |       |
| Forward Transconductance                   | $g_{FS}$         | $V_{DS} = 1.5\text{ V}, I_D = 15\text{ A}$              |     | 60  |     | S     |

## CHARGES AND CAPACITANCES

|                              |              |                                                                  |  |      |  |    |
|------------------------------|--------------|------------------------------------------------------------------|--|------|--|----|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 15\text{ V}$    |  | 3250 |  | pF |
| Output Capacitance           | $C_{OSS}$    |                                                                  |  | 1340 |  |    |
| Reverse Transfer Capacitance | $C_{RSS}$    |                                                                  |  | 90   |  |    |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}; I_D = 30\text{ A}$ |  | 22.6 |  | nC |
| Threshold Gate Charge        | $Q_{G(TH)}$  |                                                                  |  | 2.9  |  |    |
| Gate-to-Source Charge        | $Q_{GS}$     |                                                                  |  | 7.0  |  |    |
| Gate-to-Drain Charge         | $Q_{GD}$     |                                                                  |  | 6.9  |  |    |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V}, I_D = 30\text{ A}$  |  | 47.9 |  | nC |

## SWITCHING CHARACTERISTICS (Note 4)

|                     |              |                                                                                           |  |      |  |    |
|---------------------|--------------|-------------------------------------------------------------------------------------------|--|------|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V}, I_D = 15\text{ A}, R_G = 3.0\text{ }\Omega$ |  | 13.5 |  | ns |
| Rise Time           | $t_r$        |                                                                                           |  | 24.9 |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                           |  | 28.7 |  |    |
| Fall Time           | $t_f$        |                                                                                           |  | 10.7 |  |    |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

4. Switching characteristics are independent of operating junction temperatures.

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## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### SWITCHING CHARACTERISTICS (Note 4)

|                     |              |                                                                                         |  |      |  |    |
|---------------------|--------------|-----------------------------------------------------------------------------------------|--|------|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$<br>$I_D = 15\text{ A}, R_G = 3.0\ \Omega$ |  | 9.4  |  | ns |
| Rise Time           | $t_r$        |                                                                                         |  | 16.7 |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |                                                                                         |  | 35.2 |  |    |
| Fall Time           | $t_f$        |                                                                                         |  | 7.4  |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |          |                                                                                  |                           |  |      |     |    |
|-------------------------|----------|----------------------------------------------------------------------------------|---------------------------|--|------|-----|----|
| Forward Diode Voltage   | $V_{SD}$ | $V_{GS} = 0\text{ V},$<br>$I_S = 2\text{ A}$                                     | $T_J = 25^\circ\text{C}$  |  | 0.4  | 0.7 | V  |
|                         |          |                                                                                  | $T_J = 125^\circ\text{C}$ |  | 0.32 |     |    |
| Reverse Recovery Time   | $t_{RR}$ | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s},$<br>$I_S = 2\text{ A}$ |                           |  | 45   |     | ns |
| Charge Time             | $t_a$    |                                                                                  |                           |  | 23   |     |    |
| Discharge Time          | $t_b$    |                                                                                  |                           |  | 22   |     |    |
| Reverse Recovery Charge | $Q_{RR}$ |                                                                                  |                           |  | 50   |     | nC |

### PACKAGE PARASITIC VALUES

|                   |       |                          |  |      |  |          |
|-------------------|-------|--------------------------|--|------|--|----------|
| Source Inductance | $L_S$ | $T_A = 25^\circ\text{C}$ |  | 0.65 |  | nH       |
| Drain Inductance  | $L_D$ |                          |  | 0.20 |  |          |
| Gate Inductance   | $L_G$ |                          |  | 1.5  |  |          |
| Gate Resistance   | $R_G$ |                          |  | 1.0  |  | $\Omega$ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

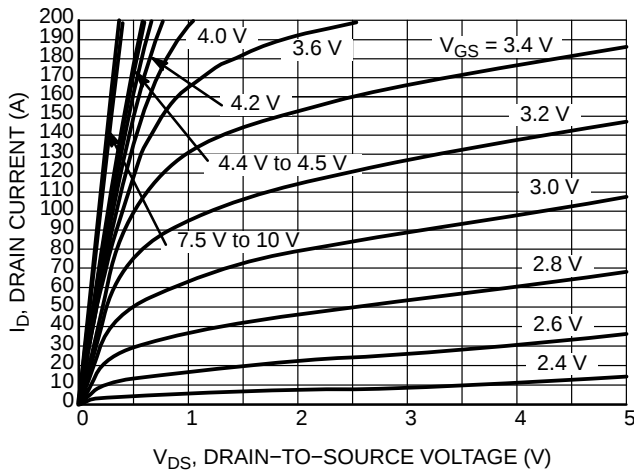


Figure 1. On-Region Characteristics

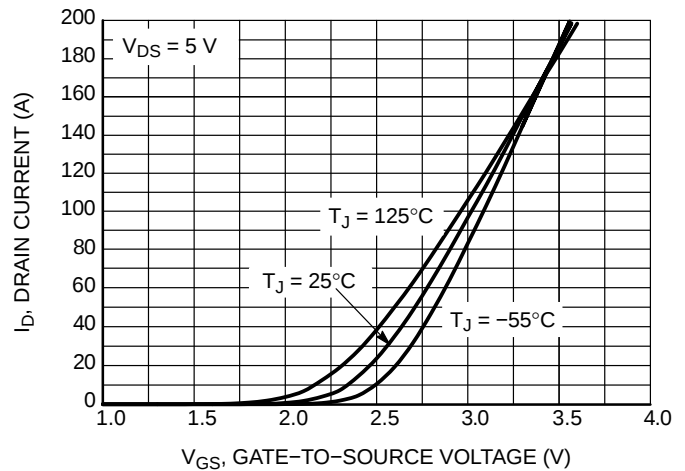


Figure 2. Transfer Characteristics

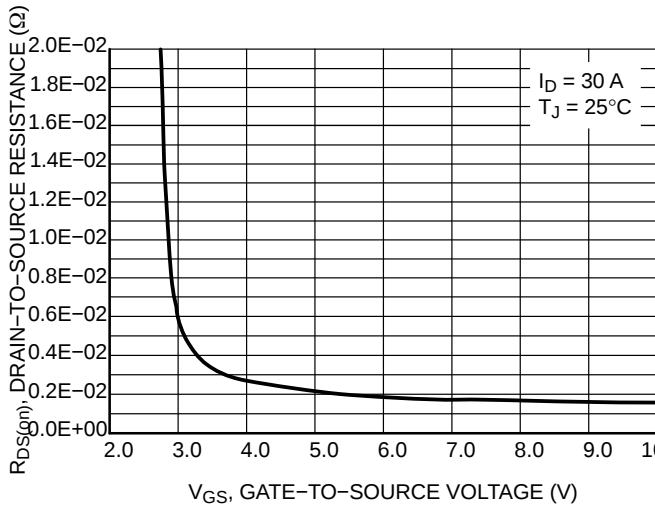


Figure 3. On-Resistance vs. Gate-to-Source Voltage

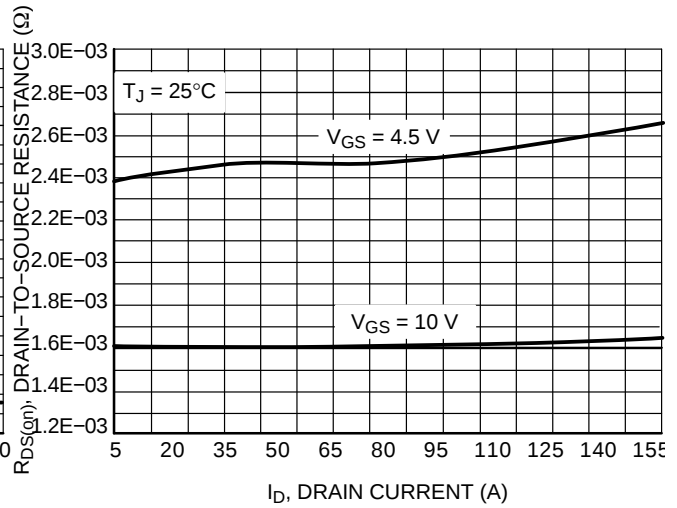


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

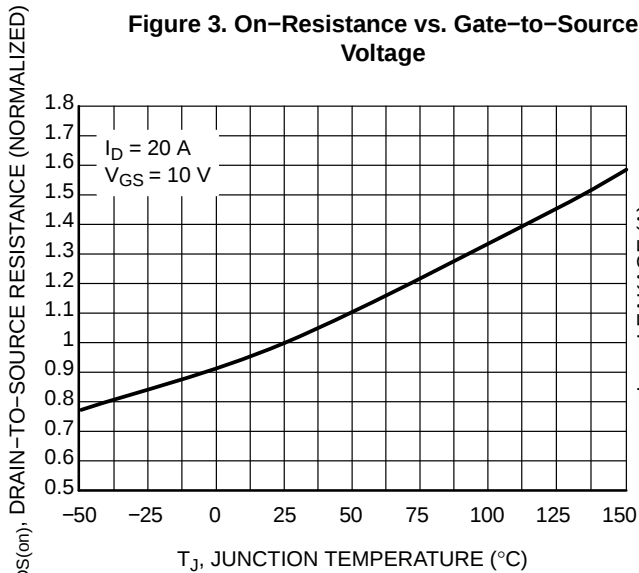


Figure 5. On-Resistance Variation with Temperature

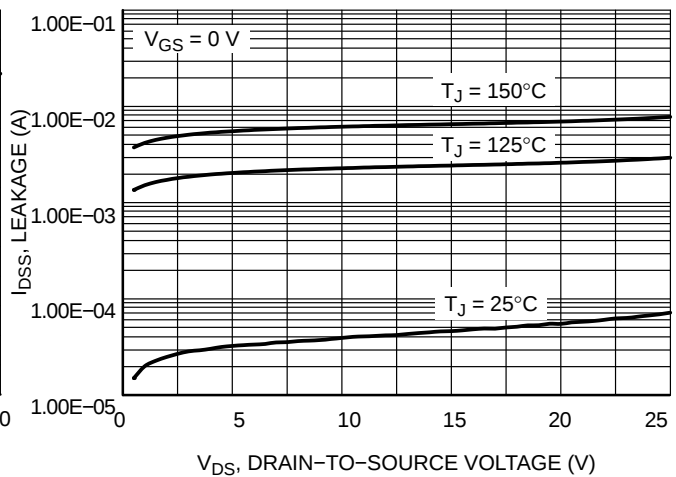


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES

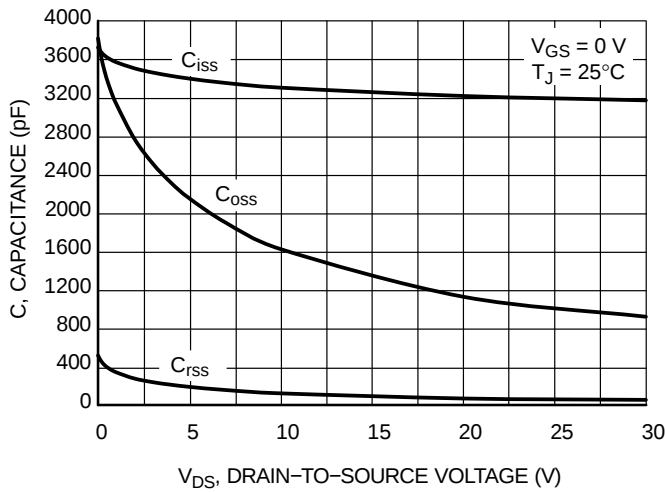


Figure 7. Capacitance Variation

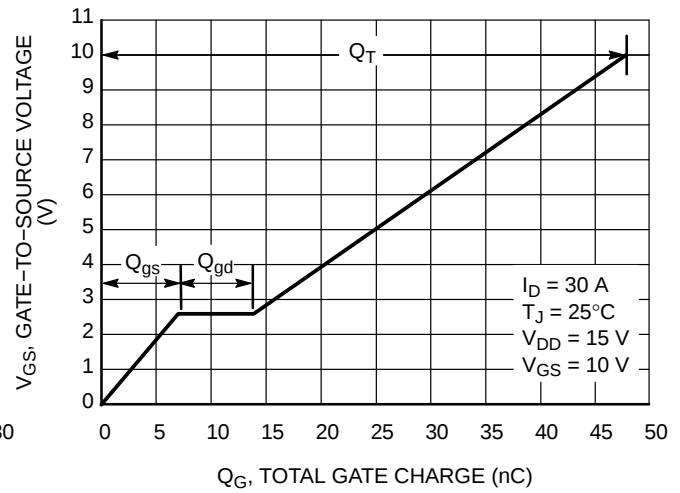


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

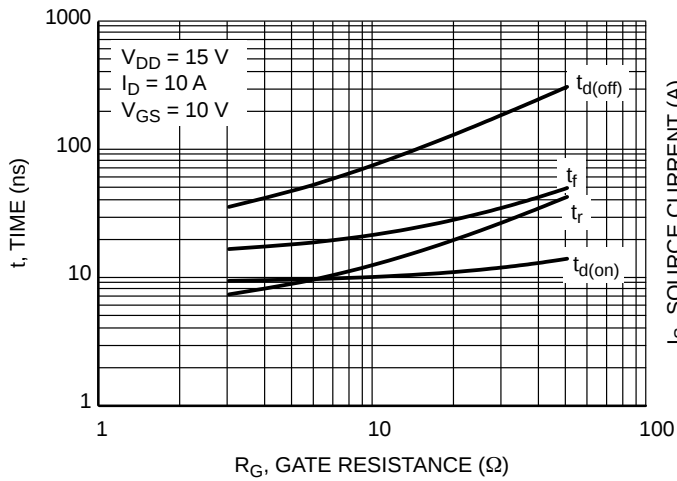


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

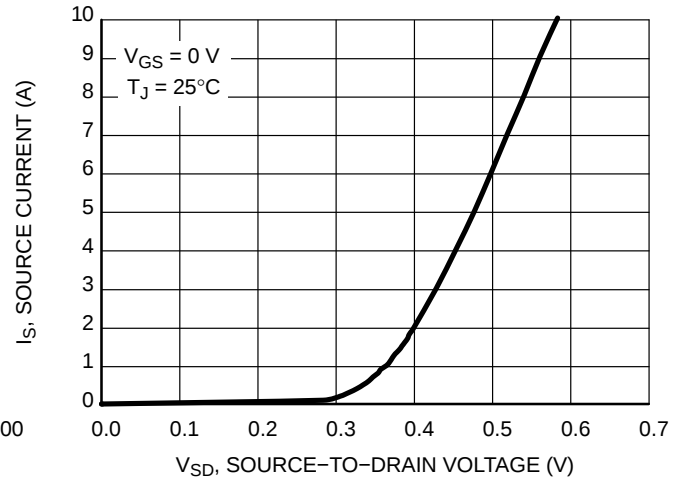


Figure 10. Diode Forward Voltage vs. Current

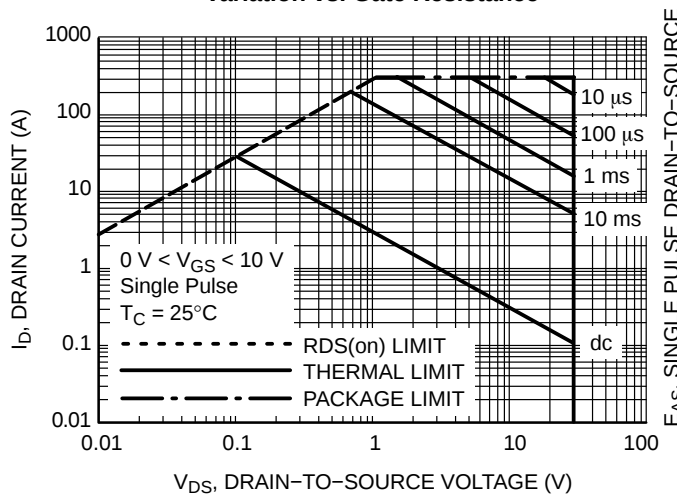


Figure 11. Maximum Rated Forward Biased Safe Operating Area

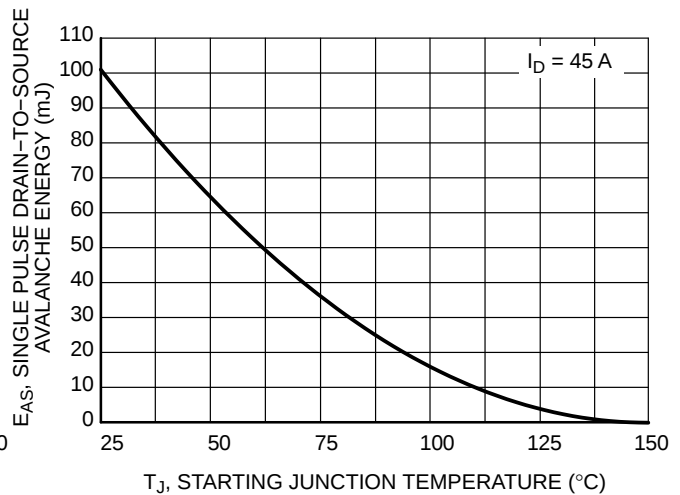


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

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## TYPICAL PERFORMANCE CURVES

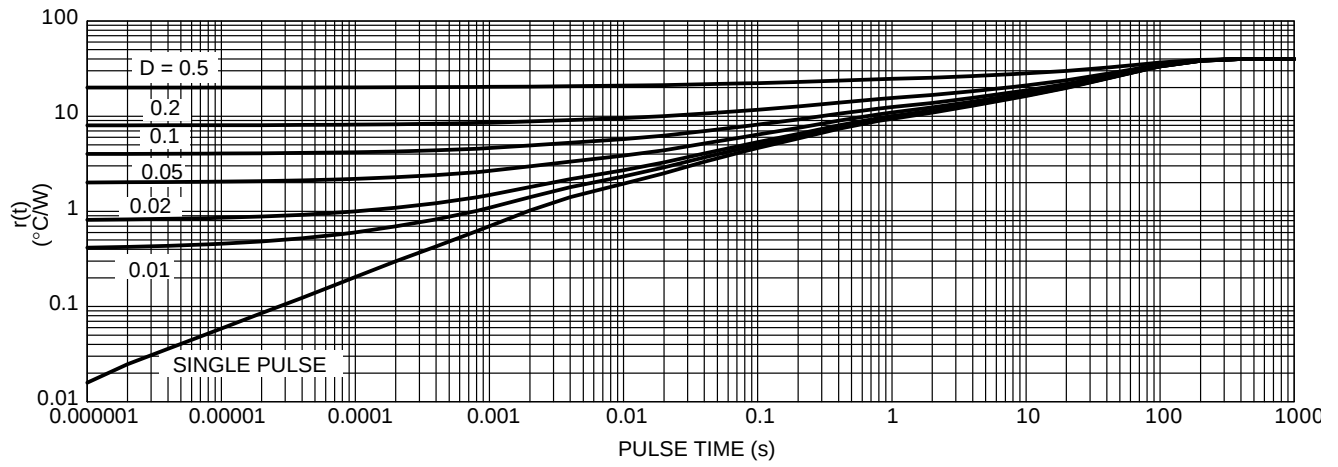
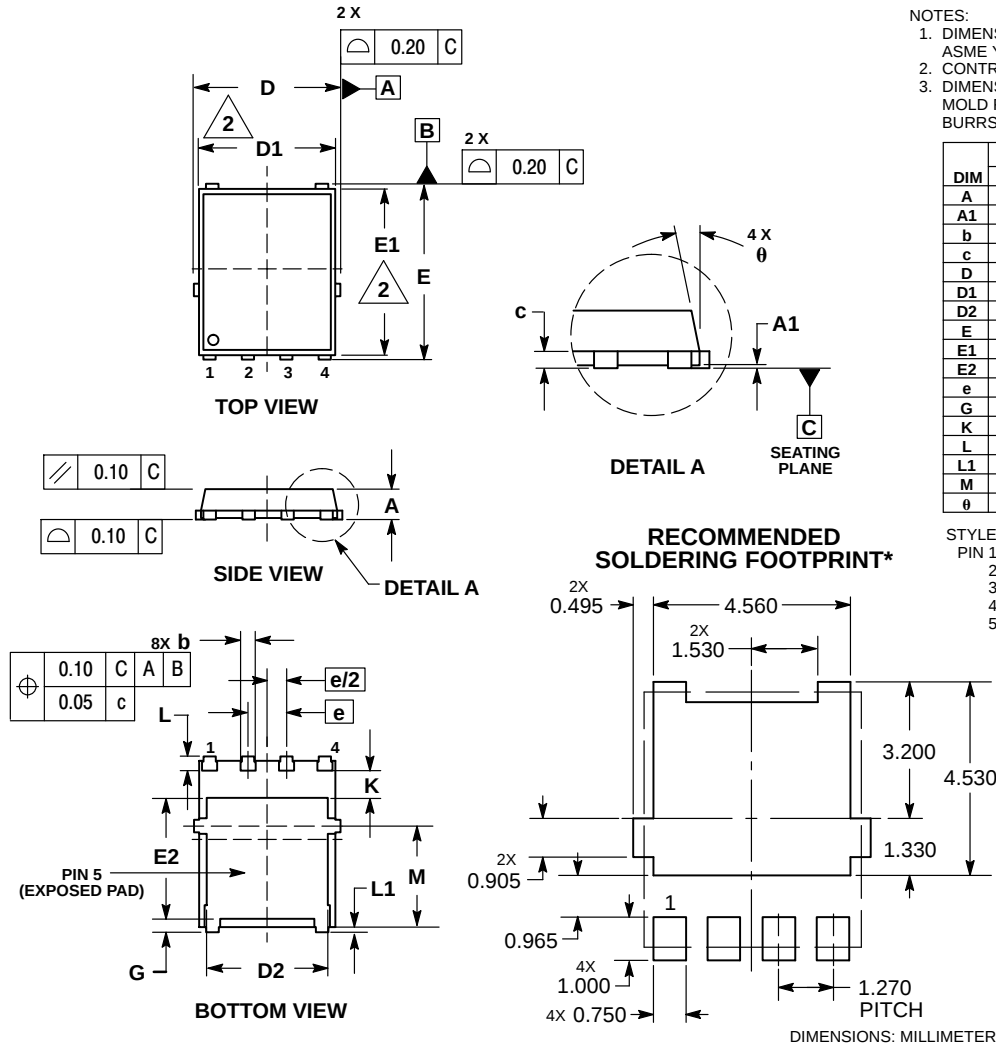


Figure 13. Thermal Response

# NTMFS4983NF

## PACKAGE DIMENSIONS

DFN5 5x6, 1.27P  
(SO-8FL)  
CASE 488AA  
ISSUE M



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

| DIM | MILLIMETERS |       |      |
|-----|-------------|-------|------|
|     | MIN         | NOM   | MAX  |
| A   | 0.90        | 1.00  | 1.10 |
| A1  | 0.00        | ---   | 0.05 |
| b   | 0.33        | 0.41  | 0.51 |
| c   | 0.23        | 0.28  | 0.33 |
| D   | 5.00        | 5.15  | 5.30 |
| D1  | 4.70        | 4.90  | 5.10 |
| D2  | 3.80        | 4.00  | 4.20 |
| E   | 6.00        | 6.15  | 6.30 |
| E1  | 5.70        | 5.90  | 6.10 |
| E2  | 3.45        | 3.65  | 3.85 |
| e   | 1.27 BSC    |       |      |
| G   | 0.51        | 0.575 | 0.71 |
| K   | 1.20        | 1.35  | 1.50 |
| L   | 0.51        | 0.575 | 0.71 |
| L1  | 0.125 REF   |       |      |
| M   | 3.00        | 3.40  | 3.80 |
| θ   | 0°          | ---   | 12°  |

STYLE 1:  
PIN 1. SOURCE  
2. SOURCE  
3. SOURCE  
4. GATE  
5. DRAIN

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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NTMFS4983NF/D



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